PA-FOC

QUERY CONTROL FORM			RTIS U	SE ONLY
Application No. 09895333	Prepared by	tw	Tracking Number	5873818
Examiner-GAU Lee-2881	Date	3-13-04	Week Date	12-8-03
	No. of queries	1		

JACKET					
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449		
b. Applicant(s)	g. Disclaimer	I. Print Fig.	q. PTOL-85b		
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract		
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs		
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other		

	YEAR
SPECIFICATION	MESSAGE
a. Page Missing	
b. Text Continuity	on Page 12, Line 16 moles a reserve to A
c. Holes through Data	ON Page 12, Line 16 moles a reprence to A Figure 1. Thould it read Figure 14.
d. Other Missing Text	
e. Illegible Text	
f. Duplicate Text	
g. Brief Description	
h. Sequence Listing	
i. Appendix	
j. Amendments	
k Other	
CLAIMS	
a. Claim(s) Missing	
b. Improper Dependency	Aleare very
c. Duplicate Numbers	Pleare very That You
d. Incorrect Numbering	initials Tw
e. Index Disagrees	RESPONSE Yes,
f. Punctuation	7
g. Amendments	
h. Bracketing	
i. Missing Text	
j. Duplicate Text	
k. Other	
	initials of L

10

15

20

5

determining, from said frequency spectrum, layer properties of layers on said part product.

Preferably, said property is one of a group comprising a thickness and a refractive index.

Preferably, said part product includes at least one at least partly transparent layer and said reflections include reflections from an upper and a lower surface of said at least partly transparent layer.

Preferably, said converting comprises producing said spectrum by Fourier transform of said analyzed intensities.

Brief Description of the Drawings

For a better understanding of the invention and to show how the same may be carried into effect, reference will now be made, purely by way of example, to the accompanying drawings, in which:

Fig. 1A is a simplified diagram of a layered wafer product,

Fig. 1B is a simplified diagram of the layered wafer product of Fig. 1 1 at a later stage in the production process,

Fig. 2 is a simplified ray diagram illustrating how light reflection can be used to obtain information of layer thicknesses in a layered wafer product,

Fig. 3 is a simplified schematic diagram of a reflection-based measuring device associated with a spinner in a semiconductor wafer production line,

de/ 3/22/04